

Serial No.:	09/870,531	Art Unit:	2827
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**IN THE TITLE**

Please amend the title to read --**Method of Manufacture of Silicon Based Package** --

**IN THE SPECIFICATION**

Please amend the paragraph [0007] beginning at page 3, line 1 to read as follows:

--[0007] U.S. patent No. 6,184,060 of Siniaguine for "Integrated Circuits and Methods for Their Fabrication" describes formation of vias and contact pads on the back side of a silicon semiconductor chip. The vias and contact pads are formed by the process starting with forming tapered vias (openings) in the back of a workpiece comprising a silicon wafer by with an isotropic plasma etch of the via opening down into the silicon wafer through an aluminum or photoresist mask formed over the silicon. The via openings have a depth at least as large as the final thickness of the wafer after the manufacturing process is completed. After the mask is removed, a thin conformal, glass or BPSG dielectric layer (1-2  $\mu\text{m}$  thick) is formed over the substrate including the vias. Then a thin conformal blanket conductive layer (e.g. 0.8-1.2  $\mu\text{m}$  thick) is formed over the dielectric layer of aluminum, gold or nickel. A planar glass layer is spun onto the surface of the conductive layer to fill the vias to provide a planar top surface of the wafer. The conductive layer may or may not have been patterned before the last step of filling the vias with the planar glass layer. Other layers to be a part of the device structure are then formed on top of the planarized surface of the workpiece including a dielectric layer and contact pads. Then the back side of the silicon wafer is etched by an atmospheric plasma etch with argon and carbon tetrafluoride in air. When the glass or BPSG dielectric layer becomes exposed, the silicon substrate is preferentially etched relative to the silicon dioxide dielectric layer by almost an order of magnitude difference with the silicon etching far more quickly. Thus, the portions of the lower surface (back side) of the conductive layer formed in the via openings comprise

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